

isc Silicon NPN Power Transistors

2SD1236L

DESCRIPTION

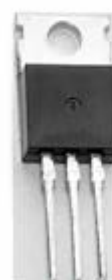
- Low Collector Saturation Voltage
: $V_{CE(sat)} = 0.4V(Max) @ I_C = 3A$
- Large Current Capacity
- Complement to Type 2SB920L
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

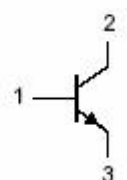
- Designed for relay drivers, high-speed inverters, converters, and other general high-current switching applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	90	V
V_{CEO}	Collector-Emitter Voltage	80	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	5	A
I_{CP}	Collector Current-Pulse	9	A
P_C	Collector Power Dissipation @ $T_a=25^{\circ}C$	1.75	W
	Collector Power Dissipation @ $T_c=25^{\circ}C$	30	
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$



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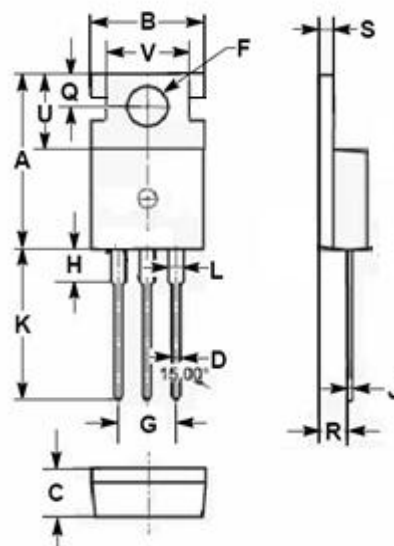


PIN 1. BASE

2. COLLECTOR

3. EMITTER

TO-220C package



DIM	mm	
	MIN	MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

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ELECTRICAL CHARACTERISTICS

T_c=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 1mA; R _{BE} = ∞	80			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = 1mA; I _E = 0	90			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 1mA; I _C = 0	6			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 3A; I _B = 0.3A			0.4	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 80V; I _E = 0			100	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = 4V; I _C = 0			100	μ A
h _{FE-1}	DC Current Gain	I _C = 1A; V _{CE} = 2V	70		280	
h _{FE-2}	DC Current Gain	I _C = 3A; V _{CE} = 2V	30			
f _T	Current-Gain—Bandwidth Product	I _C = 1A; V _{CE} = 5V		20		MHz

Switching times

t _{on}	Turn-on Time	I _C = 2A; I _{B1} = I _{B2} = 0.2A R _L = 25 Ω; P _W =20 μ s; V _{CC} = 50V		0.1		μ s
t _{stg}	Storage Time			1.2		μ s
t _f	Fall Time			0.4		μ s

◆ h_{FE-1} Classifications

Q	R	S
70-140	100-200	140-280

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